

ABSTRACT

A large-area high-output infrared detecting device S is realized in which a heat-separation-structure diaphragm 2 made of a thermal insulating material is formed through a cavity 7 from a silicon substrate 1, a thermocouple 4 serving as an infrared detection section is formed on the diaphragm 2, a heat absorption area 5 is formed on the thermocouple 4 through insulation layers 3a and 3b so as to have an etching aperture 9 for forming a cavity in the heat absorption area 5, and the cavity 7 is formed in a short time without being influenced by the size of the heat absorption area 5 to secure a structural strength.